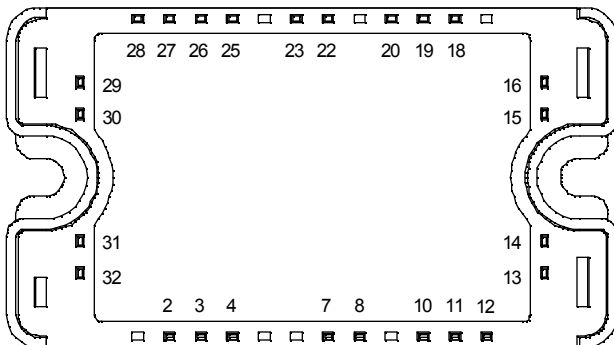
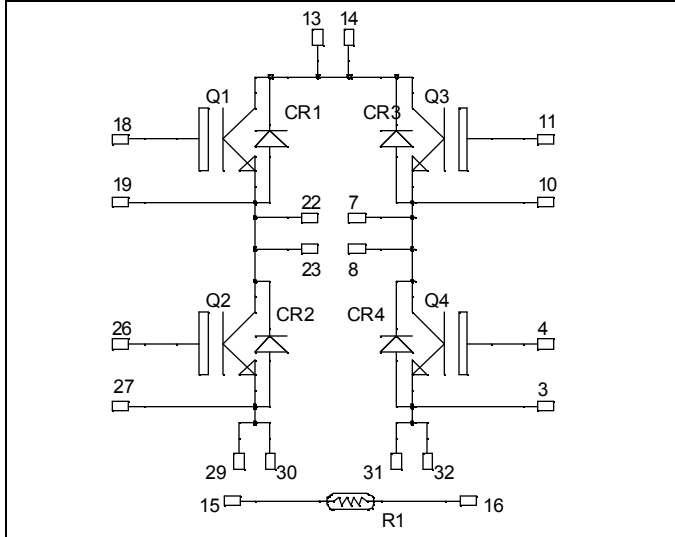


**Full - Bridge
Fast Trench + Field Stop IGBT®
Power Module**

**$V_{CES} = 1200V$
 $I_C = 50A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_C of V_{CESat}
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

| Symbol | Parameter | Max ratings | Unit |
|-----------|---------------------------------------|---------------------|--------------|
| V_{CES} | Collector - Emitter Breakdown Voltage | 1200 | V |
| I_C | Continuous Collector Current | $T_C = 25^\circ C$ | 75 |
| | | $T_C = 80^\circ C$ | 50 |
| I_{CM} | Pulsed Collector Current | $T_C = 25^\circ C$ | 100 |
| V_{GE} | Gate - Emitter Voltage | ± 20 | V |
| P_D | Maximum Power Dissipation | $T_C = 25^\circ C$ | 270 |
| RBSOA | Reverse Bias Safe Operating Area | $T_J = 125^\circ C$ | 100A @ 1150V |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

| <i>Symbol</i> | <i>Characteristic</i> | <i>Test Conditions</i> | | <i>Min</i> | <i>Typ</i> | <i>Max</i> | <i>Unit</i> |
|---------------|--------------------------------------|---|---------------------------|------------|------------|------------|---------------|
| I_{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$ | $T_j = 25^\circ\text{C}$ | | | 250 | μA |
| | | | $T_j = 125^\circ\text{C}$ | | | 500 | |
| $V_{CE(sat)}$ | Collector Emitter saturation Voltage | $V_{GE} = 15\text{V}$ $I_C = 50\text{A}$ | $T_j = 25^\circ\text{C}$ | 1.4 | 1.7 | 2.1 | V |
| | | | $T_j = 125^\circ\text{C}$ | | 2.0 | | |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 2\text{mA}$ | | 5.0 | 5.8 | 6.5 | V |
| I_{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$ | | | | 400 | nA |

Dynamic Characteristics

| <i>Symbol</i> | <i>Characteristic</i> | <i>Test Conditions</i> | | <i>Min</i> | <i>Typ</i> | <i>Max</i> | <i>Unit</i> |
|---------------|------------------------------|--|---------------------------|------------|------------|------------|-------------|
| C_{ies} | Input Capacitance | $V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$ | | | 3600 | | pF |
| C_{rss} | Reverse Transfer Capacitance | $f = 1\text{MHz}$ | | | 160 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (25°C) | | | 90 | | ns |
| T_r | Rise Time | $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ | | | 30 | | |
| $T_{d(off)}$ | Turn-off Delay Time | $I_C = 50\text{A}$ | | | 420 | | |
| T_f | Fall Time | $R_G = 18\Omega$ | | | 70 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (125°C) | | | 90 | | ns |
| T_r | Rise Time | $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ | | | 50 | | |
| $T_{d(off)}$ | Turn-off Delay Time | $I_C = 50\text{A}$ | | | 520 | | |
| T_f | Fall Time | $R_G = 18\Omega$ | | | 90 | | |
| E_{on} | Turn-on Switching Energy | $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ | $T_j = 125^\circ\text{C}$ | | 5 | | mJ |
| E_{off} | Turn-off Switching Energy | $I_C = 50\text{A}$ $R_G = 18\Omega$ | $T_j = 125^\circ\text{C}$ | | 5.5 | | |

Reverse diode ratings and characteristics

| <i>Symbol</i> | <i>Characteristic</i> | <i>Test Conditions</i> | | <i>Min</i> | <i>Typ</i> | <i>Max</i> | <i>Unit</i> |
|---------------|---|---|---------------------------|------------|------------|------------|---------------|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 1200 | | | V |
| I_{RM} | Maximum Reverse Leakage Current | $V_R = 1200\text{V}$ | $T_j = 25^\circ\text{C}$ | | | 250 | μA |
| | | | $T_j = 125^\circ\text{C}$ | | | 500 | |
| I_F | DC Forward Current | $T_c = 70^\circ\text{C}$ | | | 60 | | A |
| V_F | Diode Forward Voltage | $I_F = 60\text{A}$ | | | 2 | 2.5 | V |
| | | $I_F = 120\text{A}$ | | | 2.3 | | |
| | | $I_F = 60\text{A}$ | $T_j = 125^\circ\text{C}$ | | 1.8 | | |
| t_{rr} | Reverse Recovery Time | $I_F = 60\text{A}$ $V_R = 800\text{V}$ | $T_j = 25^\circ\text{C}$ | | 400 | | ns |
| | | | $T_j = 125^\circ\text{C}$ | | 470 | | |
| Q_{rr} | Reverse Recovery Charge | $di/dt = 200\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$ | | 1200 | | nC |
| | | | $T_j = 125^\circ\text{C}$ | | 4000 | | |
| E_r | Reverse Recovery Energy | $I_F = 60\text{A}$ $V_R = 800\text{V}$ $di/dt = 1000\text{A}/\mu\text{s}$ | $T_j = 125^\circ\text{C}$ | | 2.2 | | mJ |

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | Min | Typ | Max | Unit |
|--------------------|----------------------------|-----|------|-----|------|
| R ₂₅ | Resistance @ 25°C | | 50 | | kΩ |
| B _{25/85} | T ₂₅ = 298.15 K | | 3952 | | K |

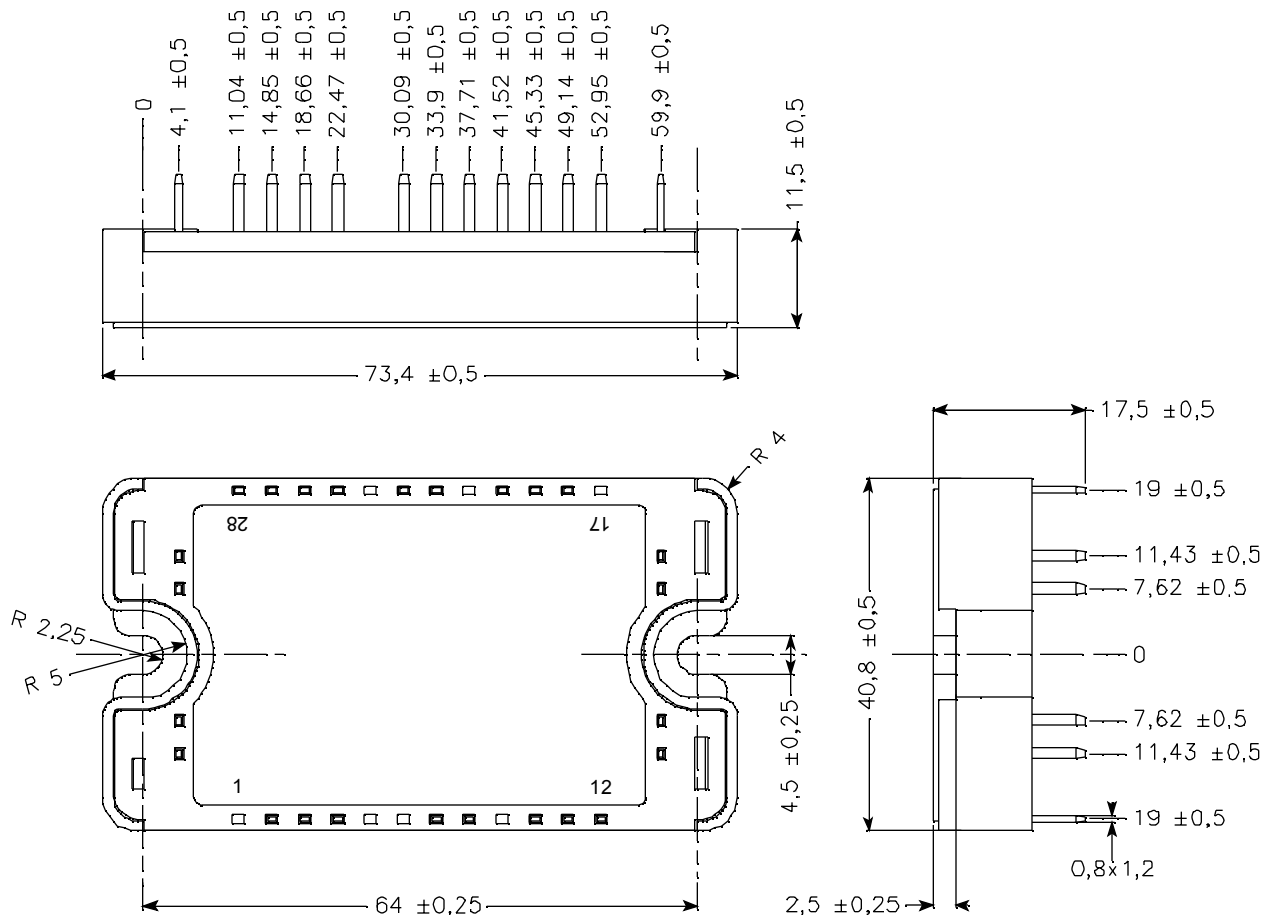
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

Thermal and package characteristics

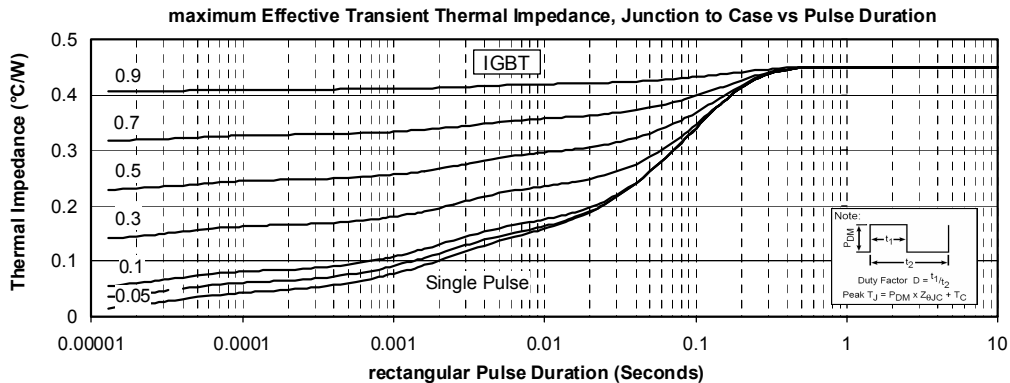
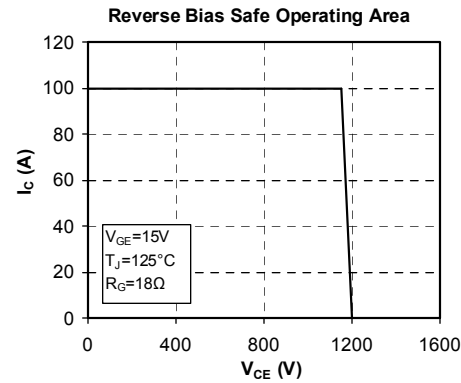
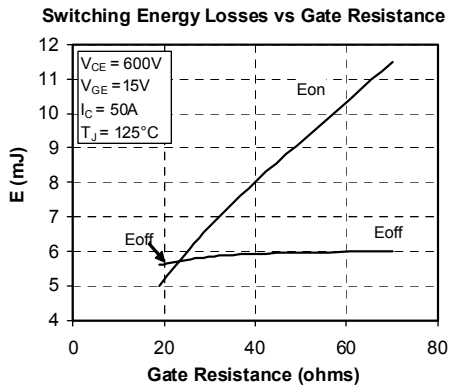
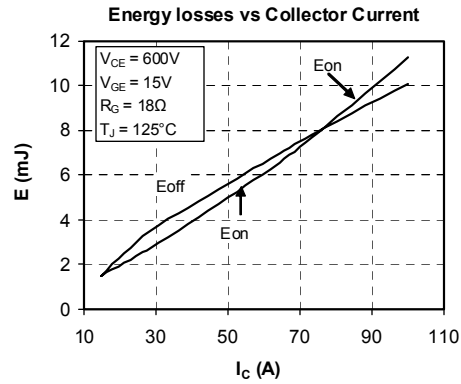
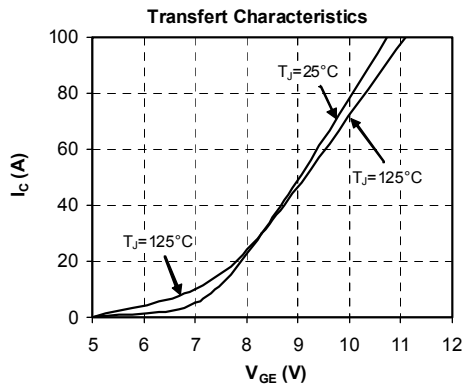
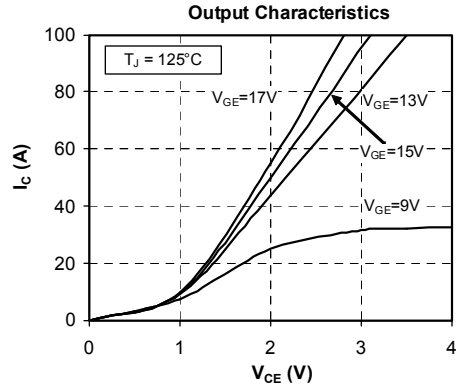
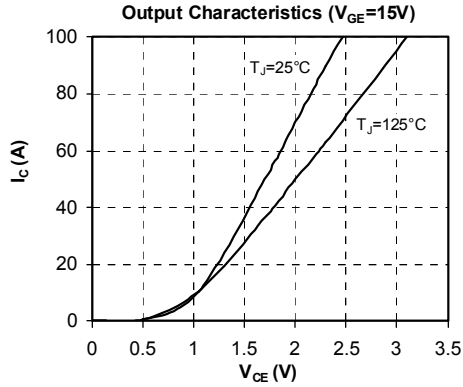
| Symbol | Characteristic | Min | Typ | Max | Unit | | |
|-------------------|--|-------|-------------|------|------|-----|-----|
| R _{thJC} | Junction to Case Thermal Resistance | IGBT | | 0.45 | °C/W | | |
| | | Diode | | 0.9 | | | |
| V _{ISOL} | RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz | 2500 | | | V | | |
| T _J | Operating junction temperature range | -40 | | 150 | °C | | |
| T _{STG} | Storage Temperature Range | -40 | | 125 | | | |
| T _C | Operating Case Temperature | -40 | | 100 | | | |
| Torque | Mounting torque | | To heatsink | M4 | 2.5 | 4.7 | N.m |
| Wt | Package Weight | | | | | 110 | g |

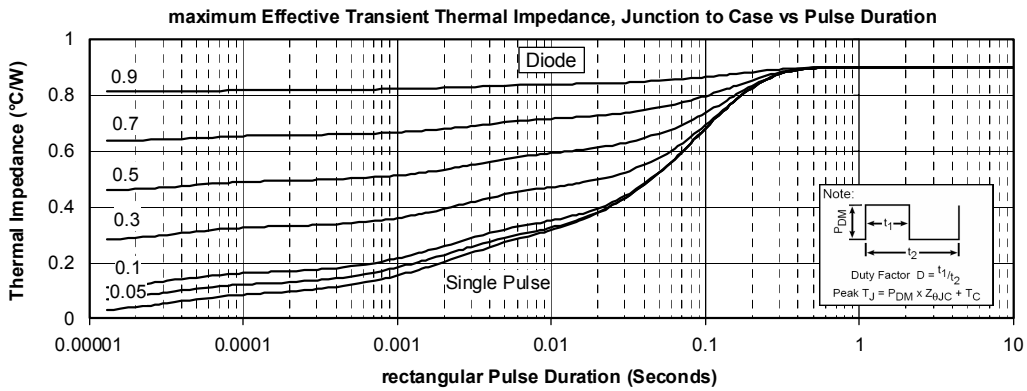
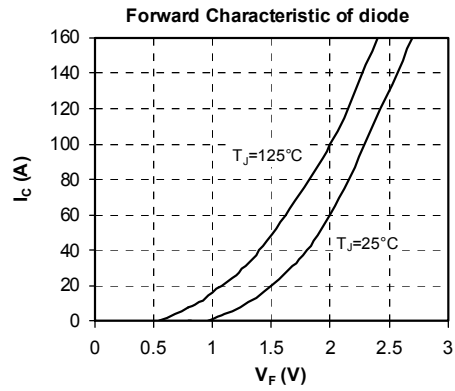
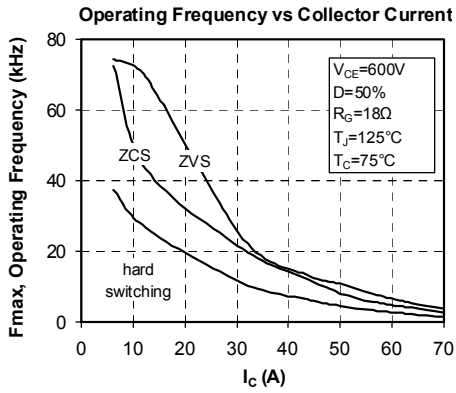
SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

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